78. (Amended) The method of claim 76 wherein exposing the wafer to a material selected from the group consisting of phosphine and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

79. (Amended) The method of claim 76 wherein exposing the wafer to a material selected from the group consisting of phosphine HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

Please add new claims 80-92 as follows:

--80. (New) The method of claim 76 wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81. (New) The method of claim 76 wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

82. (New) The method of claim 76 further comprising forming a third conductive layer on the second conductive layer.

83. (New) The method of claim 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

84. (New) The method of claim 83 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

85. (New) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer to a reducing environment;

depositing a second conductive layer; and

passivating at least one of the first and second conductive layers by exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride.

86. (New) The method of claim 85 wherein passivating at least one of the first and second conductive layers comprises exposing the wafer to the recited group prior to exposing the wafer in situ to a reducing environment.

87. (New) The method of claim 85 wherein passivating at least one of the first and second conductive layers comprises exposing the wafer to the recited group prior to depositing the second conductive layer.

88. (New) The method of claim 85 wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (New) The method of claim 85 wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (New) The method of claim 85 further comprising forming a third conductive layer on the second conductive layer.

17 16

~~91~~. (New) The method of claim ~~90~~ further comprising forming a borophosphosilicate glass layer on the third conductive layer.

18 17

~~92~~. (New) The method of claim ~~91~~ wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.--